## SiN Nanopores Enable Electrical Bar-Code Scanning of Tagged DNA

As the cost of DNA sequencing has decreased dramatically, genome sequences of numerous pathogens are readily available, and their number is growing daily. However, many pathogens are genetically similar, and differentiating between them has proven to be a difficult process with current methods. To facilitate more timely, economical, and accurate investigation of infectious agents, laboratories around the world are investigating various purely electrical schemes of detecting proteins. In the February 10 issue of Nano Letters (DOI: 10.1021/nl00058y; p. 738), A. Meller and M. Frank-Kamenetskii, professors at Boston University (BU), and their co-workers have introduced just such a technology: By electrostatically pulling a tagged, doublestranded DNA strand through a nanoscale opening on a chip, they detect changes in ion current that discriminate between tagged and untagged sites.

The researchers milled single 4–5 nm diameter nanopores in 30-nm thick freestanding SiN membranes using focused electron beam lithography. The 20  $\mu$ m by 20  $\mu$ m membrane with the pore is embedded on a 25 mm<sup>2</sup> silicon chip that separates two miniature fluid chambers filled with a 1 M solution of KCl. When a positive bias voltage is applied across the membrane, the DNA, which holds a negative charge, threads through the nanopore. This opening is just large enough to allow the molecule to pass through it without bunching (see Figure 1).

Senior research associate H. Kuhn prepared DNA molecules, which contain specific sequences bound to peptide nucleic acid (PNA) probes. As the DNA



Figure 1. Schematic depicts a DNA molecule with two peptide nucleic acid (PNA) probes threaded through a 4–5 nm nanopore in a 30-nm thick free-standing silicon nitride membrane under a voltage bias. Inset: A transmission electron microscope image of a 4 nm nanopore. Reproduced with permission from *Nano Letters* **10** (2) (2010) 738; DOI: 10.1021/nl100058y. © 2010 American Chemical Society.

threads through the nanopore, the molecules partially block the opening between the chambers which reduces the ion current between them. Because the PNAtagged regions have a greater crosssectional area than the bare DNA, as these sites pass through the membrane they increase the resistance of the nanoscale feature. The resultant change in the current was easily detected in work by graduate students A. Singer and W. Morrison and research associate M. Wanunu. Tests with control samples showed that there were no effects due to non-specific binding. Furthermore, the technique was able to distinguish between once-tagged and twice-tagged samples.

The research team said that given the known sequences, it is possible to develop a bar-coding method with the highly specific PNA, and then readout that barcode with the solid-state nanopore. Through proper tagging, it is possible to create unique single-molecule signatures that are easily identified as they pass through the nanopore. This method would dramatically improve pathogen detection in a diagnostic setting, ultimately improving patients' outcomes.

JIM RANTSCHLER

## Study of Mesoscale Epitaxy Using Colloidal Particles Reveals Dynamics Similar to Atomic-Scale Film Growth

Epitaxial film growth is a widespread and powerful fabrication method in modern materials research. Research into the physical principles that govern the growth of surface films atop a template crystalline substrate has enabled scientists to more effectively predict and design materials that possess desirable properties. In the January 22 issue of *Science* (DOI: 10.1126/science.1179947; p. 445), researchers at Cornell University report that many of the same rules that govern atomic-scale epitaxial film growth also apply to surface layers grown epitaxially using colloidal particles, although the difference in size scale introduces some mechanistic differences. Their findings should enable better modeling and prediction tools to be developed for the growing community of metamaterials researchers, and further experiments using their model system may also prove useful to researchers working at the atomic scale. Other applications of these findings may be found in the design of self-assembled nanomaterials or biologically based materials.

In order to quantify the kinetics of epitaxial growth at the microscale, I. Cohen and postdoctoral associate R. Ganapathy, together with graduate students M.R. Buckley and S.J. Gerbode, first prepared substrates with square or triangular lattices by depositing colloidal monolayers atop a lithographically patterned template with artificial lattice spacings of ~1  $\mu$ m. Subsequent layers of colloids were sedimented at a controlled rate on top of these substrates while the movement of individual particles and growth of layers were observed microscopically over time.

The researchers tested two colloid systems, consisting of either chargestabilized silica ( $1.0 \mu m$  diameter) or polystyrene colloids ( $1.3 \mu m$  diameter) particles in polymer solutions that introduced interparticle attractive forces by acting as a depletant. In order to compare their experimental results to existing models, the researchers designed their colloidal deposition solutions with diffusion constant: deposition flux (D/F) ratios on the same order as atomic-scale systems.

Using this system, the research team

observed kinetic phenomena remarkably analogous to those reported for atomicscale systems, including parameters for stable nucleation and island growth as well as the existence of step-corner and step-edge kinetic barriers. The researchers said that although atomic-scale kinetic models successfully predict much of the

## Radial *p-n* Junction Enhances Light-Trapping in Si Nanowire Solar Cells

When used in combination with inexpensive substrates to reduce the fabrication cost of photovoltaic cells, thinfilm semiconducting materials must possess either a high absorption coefficient or excellent light-trapping capabilities to overcome the resulting short optical path length and minority carrier diffusion length. While solar cells with nanostructured radial *p-n* junctions are known to have low reflective losses compared to their planar counterparts, their lighttrapping properties have not been measured. E. Garnett and P. Yang at the University of California, Berkeley, however, have recently developed a simple and scalable method to fabricate large-area silicon nanowire radial p-n junction photovoltaics (with efficiencies between 5–6%) and have quantitatively measured extraordinary enhancements in the lighttrapping path length of up to a factor of 73, which is beyond the randomized scattering (Lambertian) limit.

As described in the January 28 online edition of *Nano Letters* (DOI: 10.1021/

observed behavior, the actual forces governing the behavior are likely to be significantly different due to the change in size scale. This model system has also been artificially constrained to mimic the behavior of atomic monolayers, and the familiar phenomena observed for this system may not apply more generally to

nl100161z), the processing of these ordered nanowire arrays involves dip coating *n*-type silicon substrates to selfassemble silica spheres, deep reactive ion etching (DRIE) to form the arrays, bead removal in hydrofluoric acid, and boron diffusion to form the radial *p*-*n* junctions. The resulting nanowire arrays showed excellent packing and uniformity that extends over large areas (up to  $10 \text{ cm}^2$ ). To mimic the photovoltaic response of very thin (8 µm and 20 µm) silicon solar cells, very highly doped *n*-type silicon wafers topped with a thin, lightly doped epitaxial layer were used as the substrates. In addition, this simple method of varying the thickness of the silicon solar cells enabled quantitative measurement of their light trapping efficiency.

A maximum light-trapping path length enhancement factor between 1.7 and 73 (depending on the nanowire geometry) was recorded using optical transmission and photocurrent measurements. Longer nanowires led to both increased recombination and higher absorption, with the light-trapping effect dominating for the 8-µm thin silicon absorbing layers. Because of the incredible light-trapping other micro- and nanoscale-based materials systems. Nonetheless, this research points the way to more rigorous study of the mechanics behind materials designed at this intermediate size scale.

KRISTA L. NIECE

effect, the overall efficiency for the 8  $\mu$ m absorber silicon nanowire array solar cells is ~20% higher than results on 8- $\mu$ m thick silicon ribbon solar cells. Efficiencies between 5–6% were achieved for the nanowire array solar cells on 8  $\mu$ m and 20  $\mu$ m silicon absorber layers. However, it should be noted that no surface passivation (which is known to be important in high-performance planar solar cells) was performed.

The researchers said that it should, in principle, be possible to extend their fabrication approach to multicrystalline silicon (or other semiconductor) thin films deposited on low-cost substrates (such as glass, aluminum, or metallurgical grade silicon). By providing a means to reduce both the quantity and quality of the required silicon semiconductor and with the application of proper surface treatments, this ordered vertical nanowire array geometry represents an economically viable path toward the large scale implementation of high-efficiency, thin-film solar cells.

TIFFANY D. ZIEBELL



Praveen Chaudhari, former Director and Vice-President, Science, for IBM research laboratories worldwide, passed away at the age of 73 on January 13, 2010, at his home in Briarcliff Manor, New York, after a battle with

cancer. He is survived by his widow, Karin, son, Ashok, and daughter, Pia.

Born in Ludhiana, Punjab, India, on November 30, 1937, Praveen was educated at Indian Institute of Technology, Kharagpur, (BTech degree, 1961) and the Massachusetts Institute of Technology (PhD degree, physical metallurgy, 1966). He joined the IBM Thomas J. Watson Research Center in 1966, and enjoyed a long and extremely distinguished career as one of the foremost scientists and scientific directors in an age of extraordinary

News of MRS Members/Materials Researchers ari, innovations, many of which he helped fice-bring about. Perhaps his greatest scientific for breakthrough, along with two other IBM ries researchers, was the discovery of magnetovay optic materials that significantly impacted an-the optical data storage industry. In recognition of this seminal work, he was awarded the National Medal of Techwith nology by President Bill Clinton in 1995.

He made important contributions to many other areas of science, including structure and properties of amorphous solids, defects in solids, quantum transport in disordered systems, liquid crystal alignment on substrates, and high temperature superconductivity. Soon after the discovery of superconductivity above liquid nitrogen temperature in the cuprate superconductor YBa<sub>2</sub>Cu<sub>3</sub>O<sub>7- $\delta$ </sub> (YBCO), Praveen and his IBM colleagues demonstrated the growth of epitaxial films of this material that could sustain very high critical current densities (105-106 A/cm2 at 77 K), more than enough for practical applications. This was quickly followed by the conclusive confirmation of the deleterious influence of grain boundaries in YBCO and other superconducting cuprates in limiting the critical current density. Working with a group of talented visiting scientists and colleagues at IBM, Praveen made the ingenious use of bicrystal strontium titanate substrates to show that the superconducting coupling across a grain boundary varies almost exponentially with the misorientation angle, and that large-angle boundaries can be exploited for fabricating superconducing quantum interference (SQUID) devices. Such SQUID devices are currently being used for a number of biomedical and medical imaging applications, while the promising development of high temperature superconducting cables has